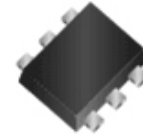
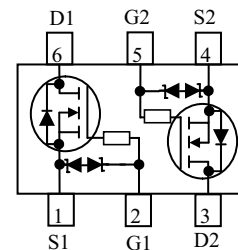


WNMD2154
Dual N-Channel, 20V, 0.88A, Small Signal MOSFET
[Http://www.willsemi.com](http://www.willsemi.com)

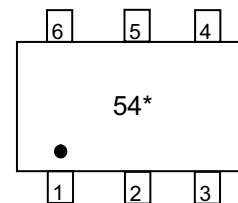
V_{DS} (V)	$R_{ds(on)}$ (Ω)
20	0.220@ $V_{GS}=4.5V$
	0.260@ $V_{GS}=2.5V$
	0.320@ $V_{GS}=1.8V$


SOT-563
Descriptions

The WNMD2154 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in DC-DC conversion, load switch and level shift. Standard Product WNMD2154 is Pb-free.


Pin configuration (Top view)
Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance
- Extremely Low Threshold Voltage
- Small package SOT-563



54 = Device Code

* = Month (A~Z)

Marking
Applications

- DC-DC converter circuit
- Load Switch
- Level Shift

Order information

Device	Package	Shipping
WNMD2154-6/TR	SOT-563	3000/Reel&Tape

Absolute Maximum ratings

Parameter		Symbol	10 S	Steady State	Unit
Drain-Source Voltage		V_{DS}	+20		V
Gate-Source Voltage		V_{GS}	± 6		
Continuous Drain Current ^a	$T_A=25^\circ\text{C}$	I_D	0.88	0.80	A
	$T_A=70^\circ\text{C}$		0.71	0.64	
Maximum Power Dissipation ^a	$T_A=25^\circ\text{C}$	P_D	0.37	0.30	W
	$T_A=70^\circ\text{C}$		0.23	0.19	
Continuous Drain Current ^b	$T_A=25^\circ\text{C}$	I_D	0.76	0.69	A
	$T_A=70^\circ\text{C}$		0.60	0.55	
Maximum Power Dissipation ^b	$T_A=25^\circ\text{C}$	P_D	0.27	0.22	W
	$T_A=70^\circ\text{C}$		0.17	0.14	
Pulsed Drain Current ^c		I_{DM}	1.4		A
Operating Junction Temperature		T_J	150		$^\circ\text{C}$
Lead Temperature		T_L	260		$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150		$^\circ\text{C}$

Thermal resistance ratings

Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ^a	$t \leq 10\text{ s}$	$R_{\theta JA}$	285	335	$^\circ\text{C/W}$
	Steady State		340	405	
Junction-to-Ambient Thermal Resistance ^b	$t \leq 10\text{ s}$	$R_{\theta JA}$	385	450	
	Steady State		455	545	
Junction-to-Case Thermal Resistance		$R_{\theta JC}$	260	300	
Dual Operation					
Junction-to-Ambient Thermal Resistance ^a	$t \leq 10\text{ s}$	$R_{\theta JA}$	315	365	$^\circ\text{C/W}$
	Steady State		370	440	
Junction-to-Ambient Thermal Resistance ^b	$t \leq 10\text{ s}$	$R_{\theta JA}$	420	490	
	Steady State		505	585	
Junction-to-Case Thermal Resistance		$R_{\theta JC}$	265	305	

a Surface mounted on FR4 Board using 1 square inch pad size, 1oz copper

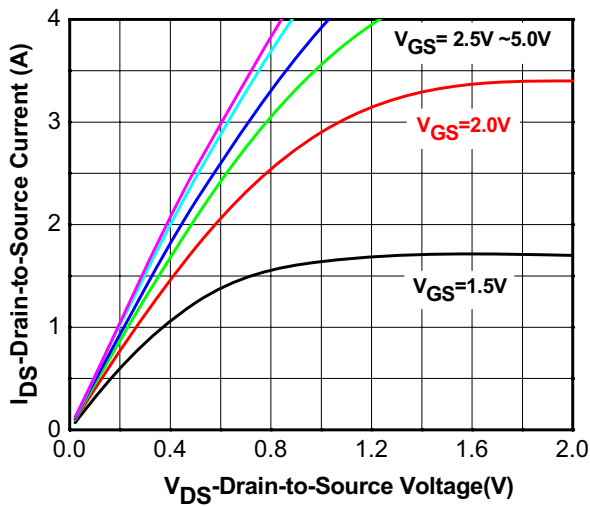
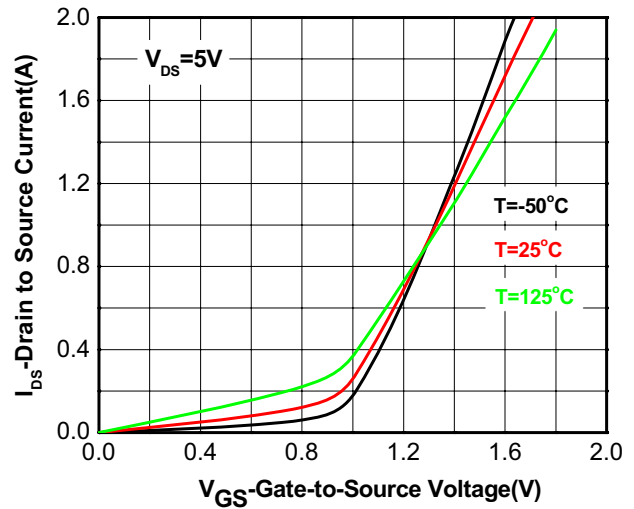
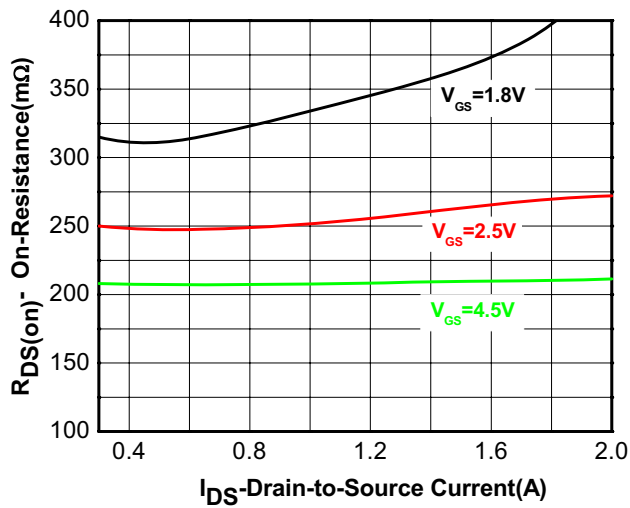
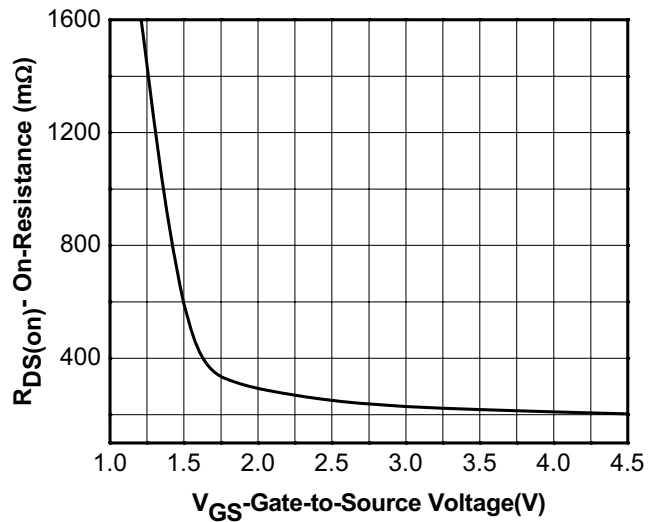
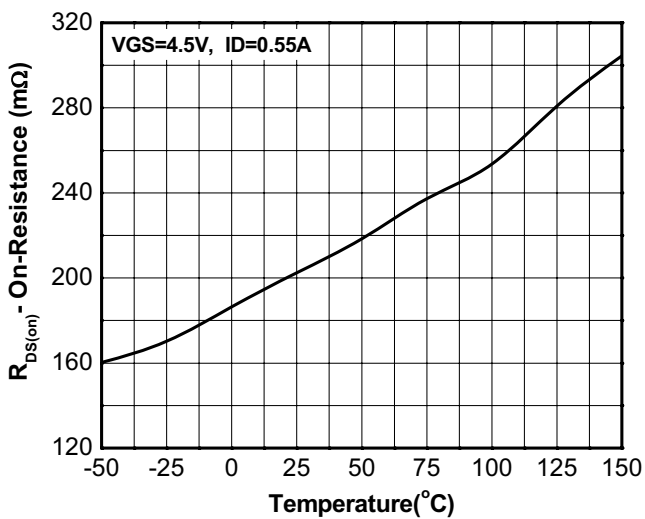
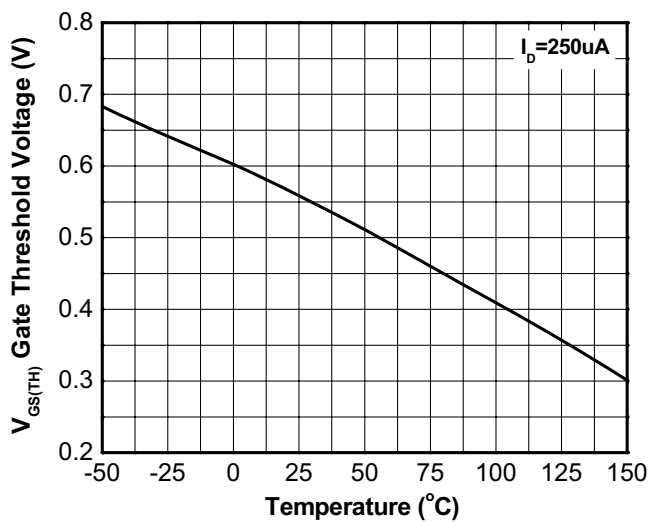
b Surface mounted on FR4 board using minimum pad size, 1oz copper

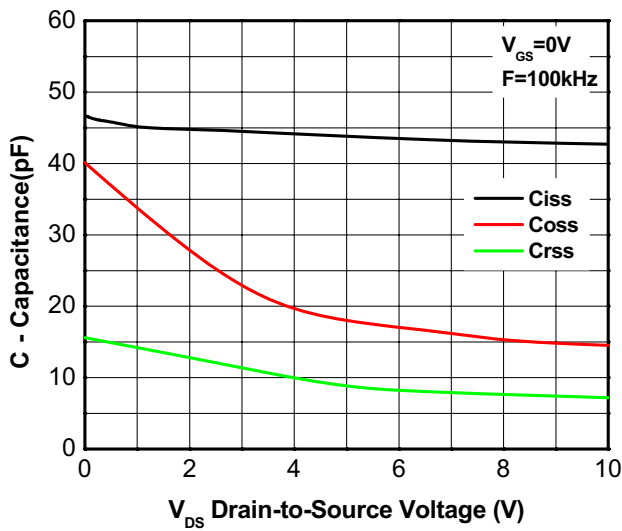
c Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

d Repetitive rating, pulse width limited by junction temperature $T_J=150^\circ\text{C}$.

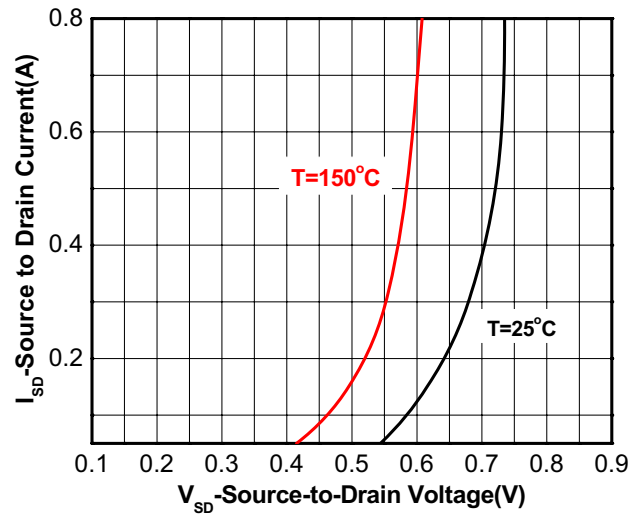
Electronics Characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{A}$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{V}$			1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{V}$			± 5	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	0.45	0.58	0.85	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS} = 4.5\text{V}, I_D = 0.55\text{A}$		220	310	m Ω
		$V_{GS} = 2.5\text{V}, I_D = 0.45\text{A}$		260	360	
		$V_{GS} = 1.8\text{V}, I_D = 0.35\text{A}$		320	460	
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 0.55\text{A}$		2.0		S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 100\text{kHz}, V_{DS} = 10\text{ V}$		60		pF
Output Capacitance	C_{OSS}			11		
Reverse Transfer Capacitance	C_{RSS}			7.5		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}, I_D = 0.55\text{A}$		1.15		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.06		
Gate-to-Source Charge	Q_{GS}			0.15		
Gate-to-Drain Charge	Q_{GD}			0.23		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_d(ON)$	$V_{DD} = 10\text{V}, V_{GS} = 4.5\text{V}, I_D = 0.55\text{A}, R_G = 6\Omega$		22		ns
Rise Time	t_r			80		
Turn-Off Delay Time	$t_d(OFF)$			700		
Fall Time	t_f			380		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 0.35\text{A}$	0.5	0.7	1.5	V

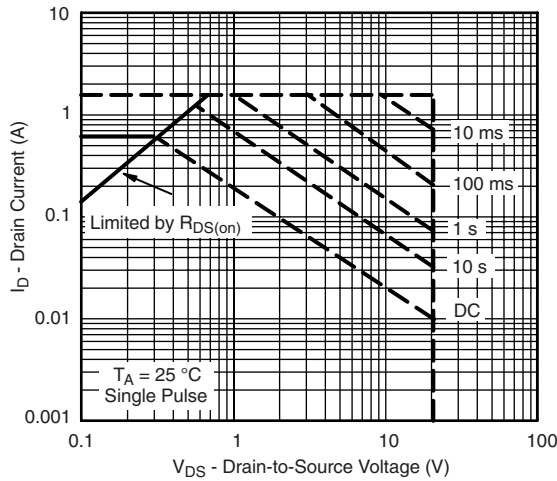
Typical Characteristics (Ta=25°C, unless otherwise noted)

Output characteristics

Transfer characteristics

On-Resistance vs. Drain current

On-Resistance vs. Gate-to-Source voltage

On-Resistance vs. Junction temperature

Threshold voltage vs. Temperature



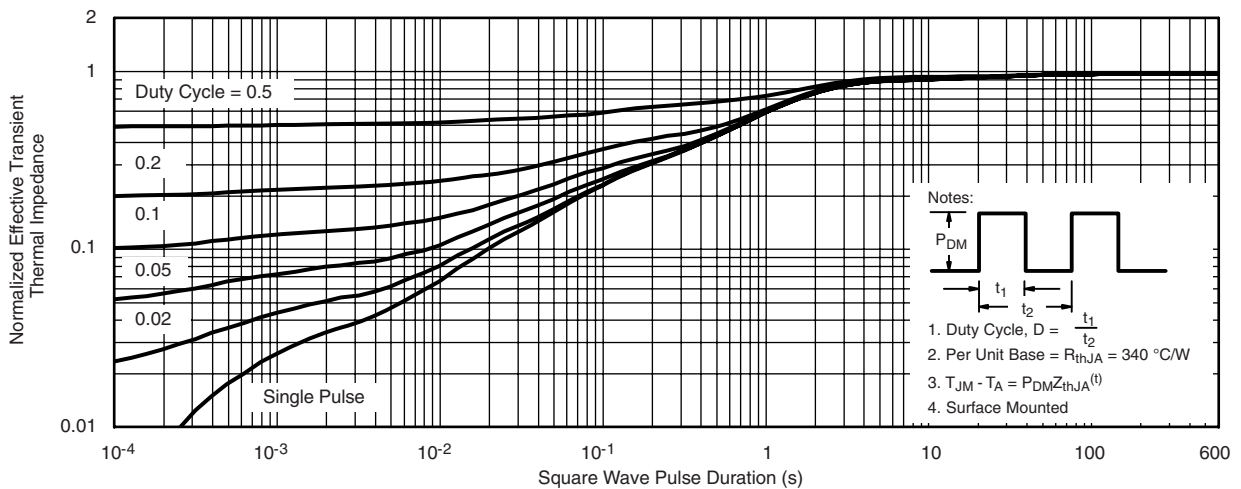
Capacitance



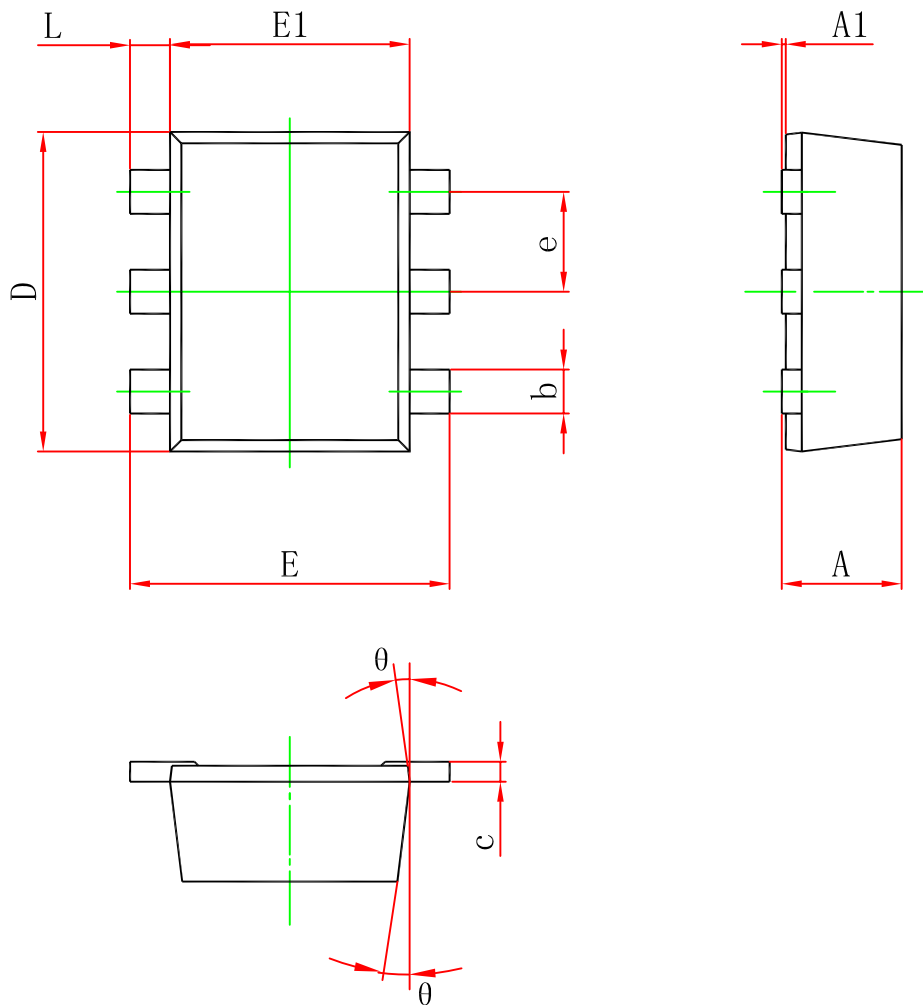
Body diode forward voltage



Safe operating power



Transient thermal response (Junction-to-Ambient)

Package outline dimensions
SOT-563


Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.525	0.563	0.600
A1	0.000	0.025	0.050
e	0.450	0.500	0.550
c	0.090	0.125	0.160
D	1.500	1.600	1.700
b	0.170	0.22	0.270
E1	1.100	1.200	1.300
E	1.500	1.600	1.700
L	0.100	0.200	0.300
θ	7° REF		